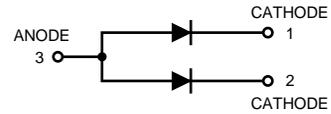


Monolithic Dual Switching Diode

MMBD2836GH



ORDERING INFORMATION

| Device | Marking | Shipping |
|--------------|---------|-----------------|
| LMBD2835LT1G | A3X | 3000/Tape&Reel |
| LMBD2835LT3G | A3X | 10000/Tape&Reel |
| LMBD2836LT1G | A2X | 3000/Tape&Reel |
| LMBD2836LT3G | A2X | 10000/Tape&Reel |

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---------------------------|--------------|-------|------|
| Peak Reverse Voltage | V_{RM} | 75 | Vdc |
| D.C Reverse Voltage | V_R | 35 | Vdc |
| | LMBD2836LT1G | 75 | |
| Peak Forward Current | I_{FM} | 450 | mAdc |
| | | 300 | |
| Average Rectified Current | I_O | 150 | mAdc |
| | | 100 | |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------|----------------------|
| Total Device Dissipation FR-5 Board ⁽¹⁾ $T_A = 25^\circ\text{C}$ | P_D | 225 | mW |
| Derate above 25°C | | 1.8 | mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 556 | $^\circ\text{C/W}$ |
| Total Device Dissipation | P_D | 300 | mW |
| Alumina Substrate, ⁽²⁾ $T_A = 25^\circ\text{C}$ | | | |
| Derate above 25°C | | 2.4 | mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 417 | $^\circ\text{C/W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

DEVICE MARKING

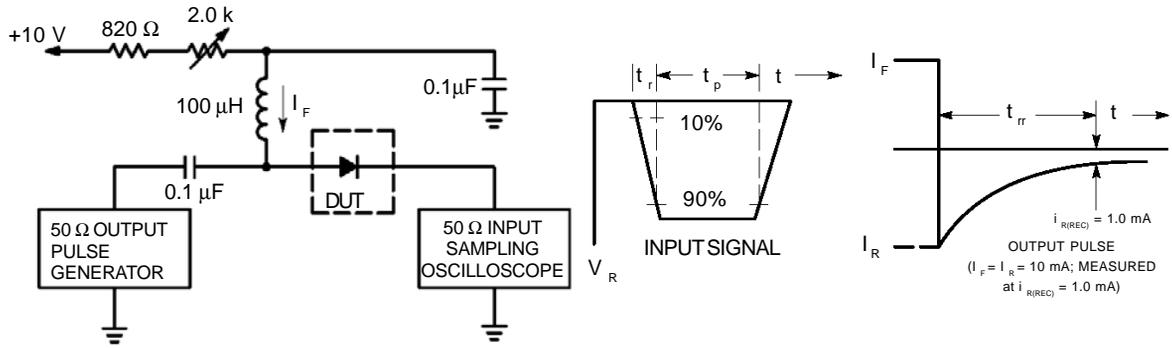
LMBD2835LT1G = A3X; LMBD2836LT1G = A2X

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

| Characteristic | Symbol | Min | Max | Unit |
|---|--------------|------------|-----|------|
| OFF CHARACTERISTICS | | | | |
| Reverse Breakdown Voltage ($I_R = 100 \mu\text{Adc}$) | LMBD2835LT1G | $V_{(BR)}$ | 35 | — |
| | LMBD2836LT1G | | 75 | — |
| Reverse Voltage Leakage Current | I_R | | | nAdc |
| ($V_R = 30 \text{ Vdc}$) | LMBD2835LT1G | — | 100 | |
| ($V_R = 50 \text{ Vdc}$) | LMBD2836LT1G | — | 100 | |
| Diode Capacitance | C_T | — | 4.0 | pF |
| ($V_R = 0, f = 1.0 \text{ MHz}$) | | | | |
| Forward Voltage ($I_F = 10 \text{ mAdc}$) | V_F | — | 1.0 | Vdc |
| ($I_F = 50 \text{ mAdc}$) | | — | 1.0 | |
| ($I_F = 100 \text{ mAdc}$) | | — | 1.2 | |
| Reverse Recovery Time ($I_F = I_R = 10 \text{ mAdc}, I_{R(REC)} = 1.0 \text{ mAdc}$) (Figure 1) | t_{rr} | — | 4.0 | ns |

1. FR-5 = 1.0 x 0.75 x 0.062 in.

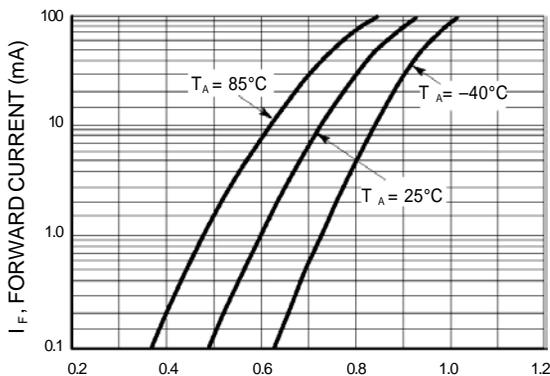
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



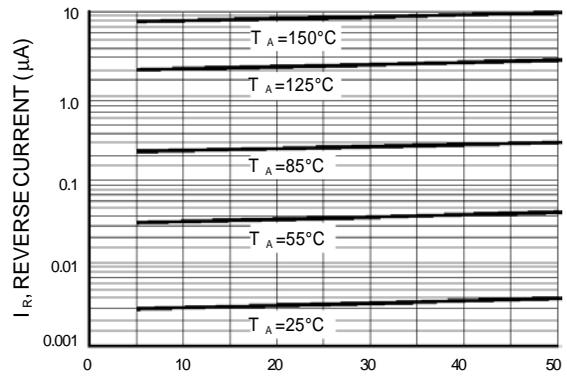
- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
- 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.
- 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

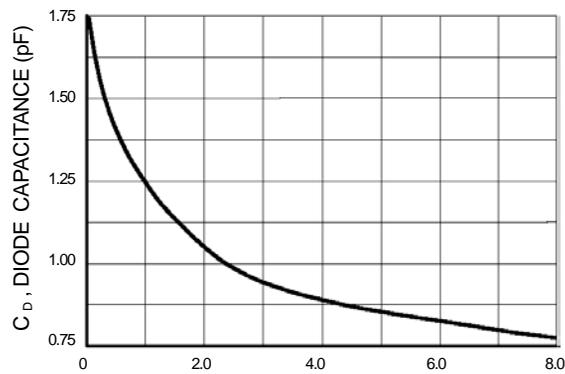
CURVES APPLICABLE TO EACH CATHODE



V_F , FORWARD VOLTAGE (VOLTS)
Figure 2. Forward Voltage



V_R , REVERSE VOLTAGE (VOLTS)
Figure 3. Leakage Current



V_R , REVERSE VOLTAGE (VOLTS)
Figure 4. Capacitance